

NZQA5V6XV5T1 Series

Quad Array for ESD Protection

This quad monolithic silicon voltage suppressor is designed for applications requiring transient overvoltage protection capability. It is intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment, and other applications. Its quad junction common anode design protects four separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features

- SOT-553 Package Allows Four Separate Unidirectional Configurations
- Low Leakage < 1 μ A @ 3 Volt for NZQA5V6XV5T1
- Breakdown Voltage: 5.6 Volt - 6.8 Volt @ 1 mA
- ESD Protection Meeting IEC61000-4-2 - Level 4

Mechanical Characteristics

- Void Free, Transfer-Molded, Thermosetting Plastic Case
- Corrosion Resistant Finish, Easily Solderable
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications
- 100% Lead Free, MSL1 @ 260°C Reflow Temperature



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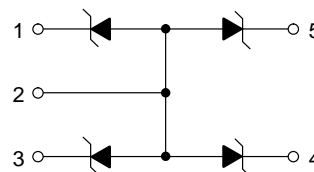


**SOT-553
CASE 463B
PLASTIC**

MARKING DIAGRAM



xx = Device Marking
D = One Digit Date Code



ORDERING INFORMATION

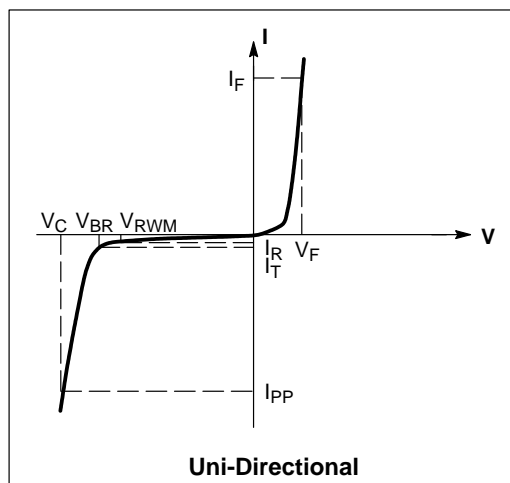
Device	Package	Shipping
NZQA5V6XV5T1	SOT-553	4000/Tape & Reel
NZQA6V2XV5T1	SOT-553	4000/Tape & Reel
NZQA6V8XV5T1	SOT-553	4000/Tape & Reel

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ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
Θ_{VBR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}



MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Power Dissipation (8 X 20 μs @ $T_A = 25^\circ\text{C}$) (Note 1)	P_{PK}	100	W
Steady State Power - 1 Diode (Note 2)	P_D	300	mW
Thermal Resistance Junction to Ambient Above 25°C , Derate	$R_{\theta JA}$	370 2.7	$^\circ\text{C/W}$ mW/ $^\circ\text{C}$
Maximum Junction Temperature	T_{Jmax}	150	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	$T_J T_{stg}$	-55 to +150	$^\circ\text{C}$
ESD Discharge MIL STD 883C - Method 3015-6 IEC1000-4-2, Air Discharge IEC1000-4-2, Contact Discharge	V_{PP}	16 16 9	kV
Lead Solder Temperature (10 seconds duration)	T_L	260	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Device	Device Marking	Breakdown Voltage V_{BR} @ 1 mA (Volts)			Leakage Current I_{RM} @ V_{RM}		V_C Max @ I_{PP}		Typ Capacitance @ 0 V Bias (Note 3) (pF)	Max V_F @ $I_F = 200$ mA (V)
		Min	Nom	Max	V_{RWM}	I_{RWM} (μA)	V_C (V)	I_{PP} (A)		
NZQA5V6XV5T1	56	5.32	5.6	5.88	3.0	1.0	10.5	10	90	1.3
NZQA6V2XV5T1	62	5.89	6.2	6.51	4.0	0.5	11.5	9.0	80	1.3
NZQA6V8XV5T1	68	6.46	6.8	7.14	4.3	0.1	12.5	8.0	70	1.3

1. Non-repetitive current per Figure 1.
2. Only 1 diode under power. For all 4 diodes under power, P_D will be 25%. Mounted on FR-4 board with min pad.
3. Capacitance of one diode at $f = 1$ MHz, $V_R = 0$ V, $T_A = 25^\circ\text{C}$

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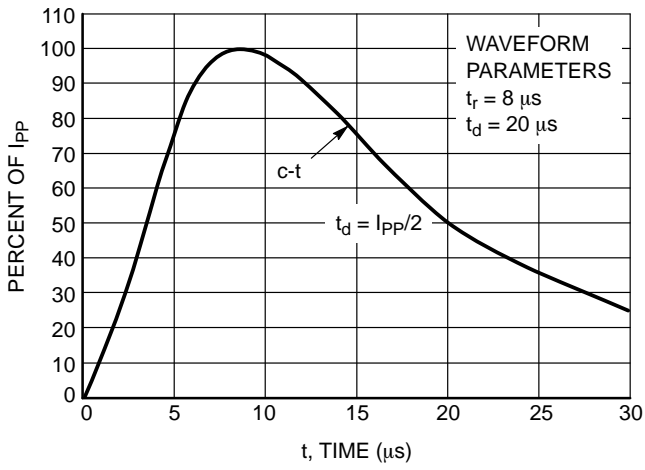


Figure 1. Pulse Waveform

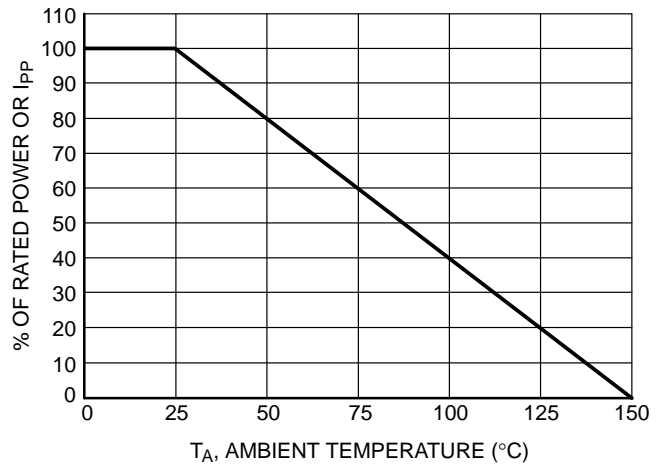


Figure 2. Power Derating Curve

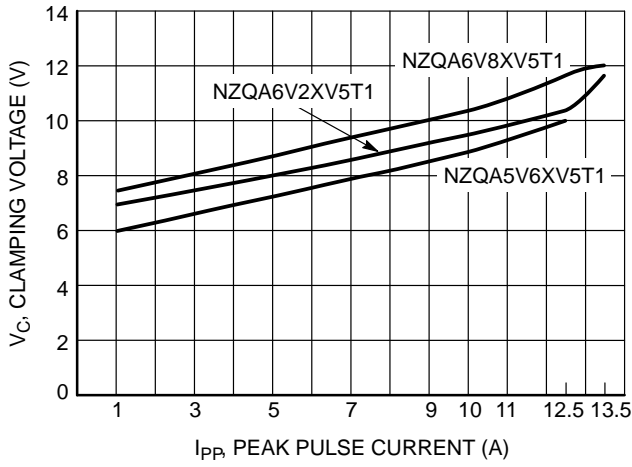


Figure 3. Clamping Voltage versus Peak Pulse Current

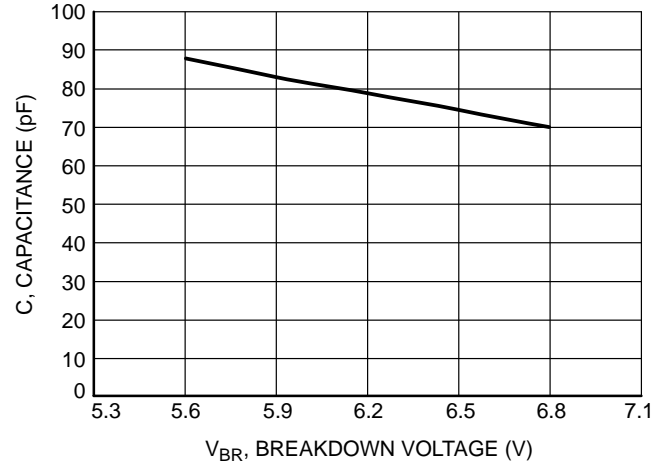
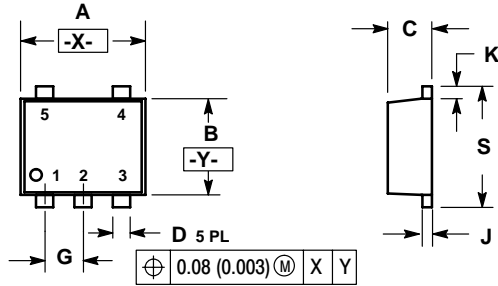


Figure 4. Typical Capacitance

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PACKAGE DIMENSIONS

SOT-553, 5-LEAD
CASE 463B-01
ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.50	1.70	0.059	0.067
B	1.10	1.30	0.043	0.051
C	0.50	0.60	0.020	0.024
D	0.17	0.27	0.007	0.011
G	0.50 BSC		0.020 BSC	
J	0.08	0.18	0.003	0.007
K	0.10	0.30	0.004	0.012
S	1.50	1.70	0.059	0.067

STYLE 1:

- PIN 1. BASE 1
- EMITTER 1/2
- BASE 2
- COLLECTOR 2
- COLLECTOR 1

STYLE 2:

- PIN 1. CATHODE
- ANODE
- CATHODE
- CATHODE
- CATHODE

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